



### General Description

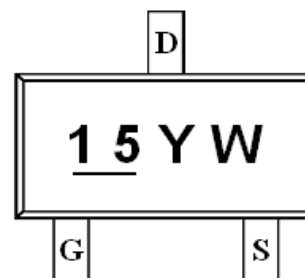
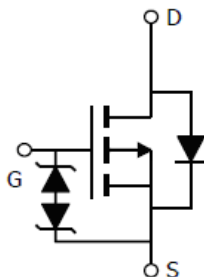
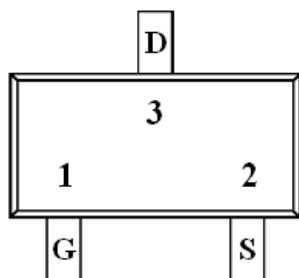
AFP3415EA, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- $I_D = -4.5A, R_{DS(ON)} = 41m\Omega @ V_{GS} = 4.5V$
- $I_D = -3.4A, R_{DS(ON)} = 54m\Omega @ V_{GS} = 2.5V$
- $I_D = -2.2A, R_{DS(ON)} = 70m\Omega @ V_{GS} = 1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- ESD Protected
- SOT-23 package design

### Pin Description ( SOT-23 )



### Application

- Portable Equipment
- Battery Powered System
- Net Working System

### Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP3415EAS23RG	15YW	SOT-23	Tape & Reel	3000 EA

- ※ 15 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFP3415EAS23RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate -Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-4.5
		T <sub>A</sub> =70°C	-3.9
Pulsed Drain Current	I <sub>DM</sub>	-10	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	1.25
		T <sub>A</sub> =70°C	0.8
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

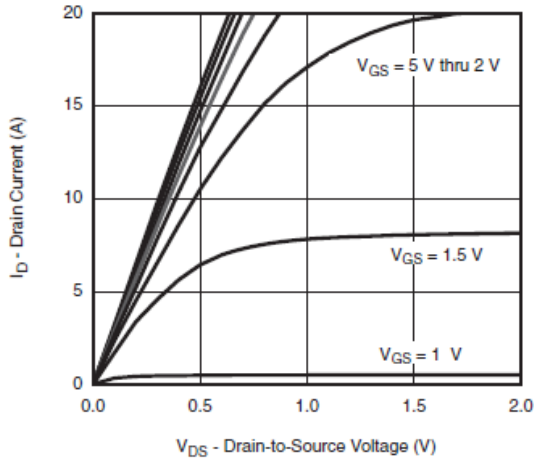
### Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

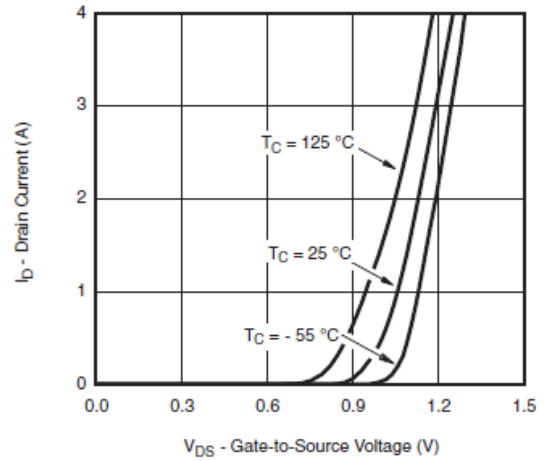
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.4	-0.6	-0.9	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±10	uA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V			-1	uA
		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -5V, V <sub>GS</sub> =-4.5V	-6			A
		V <sub>DS</sub> ≥ -5V, V <sub>GS</sub> =-2.5V	-4			
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.5A		35	41	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3.4A		45	54	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2.2A		60	70	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3.6A		10		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.25A, V <sub>GS</sub> =0V		-0.85	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-2.5V I <sub>D</sub> ≡-4.0A		10	18	nC
Gate-Source Charge	Q <sub>gs</sub>			2.5		
Gate-Drain Charge	Q <sub>gd</sub>			3.5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V f=1MHz		1050		pF
Output Capacitance	C <sub>oss</sub>			165		
Reverse Transfer Capacitance	C <sub>rss</sub>			135		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, R <sub>L</sub> =2.7Ω I <sub>D</sub> ≡-3.7A, V <sub>GEN</sub> =-4.5V R <sub>G</sub> =1Ω		15	25	ns
	t <sub>r</sub>			25	40	
Turn-Off Time	t <sub>d(off)</sub>			40	65	
	t <sub>f</sub>			15	25	



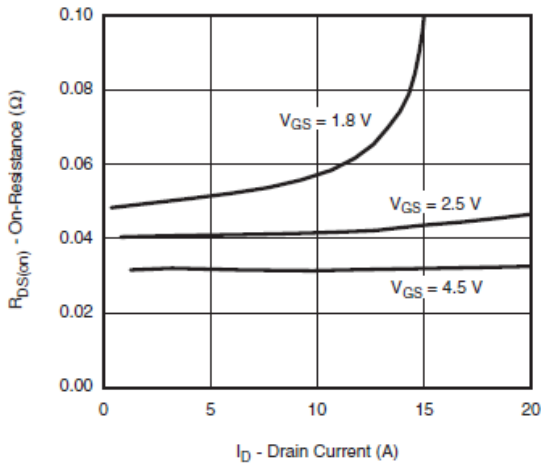
## Typical Characteristics



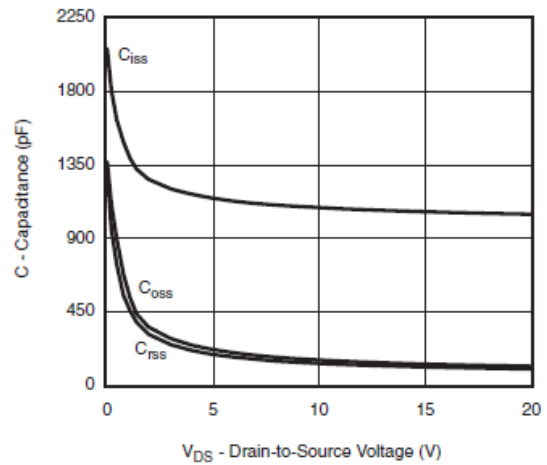
Output Characteristics



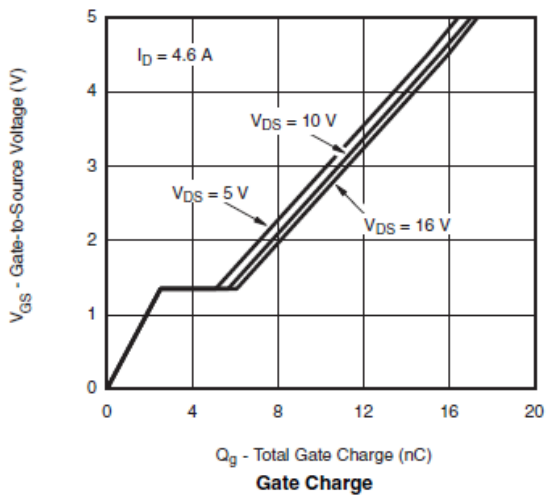
Transfer Characteristics



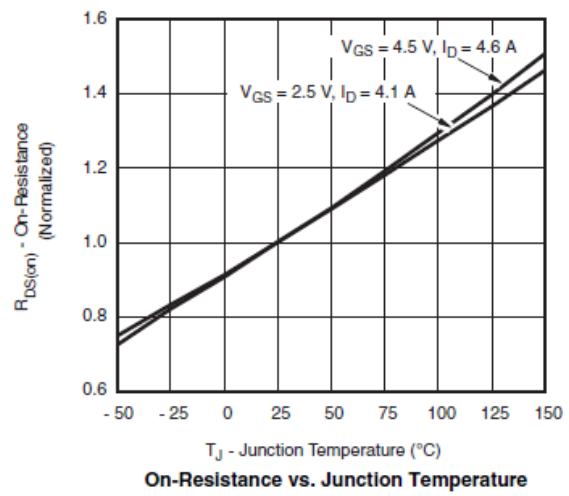
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



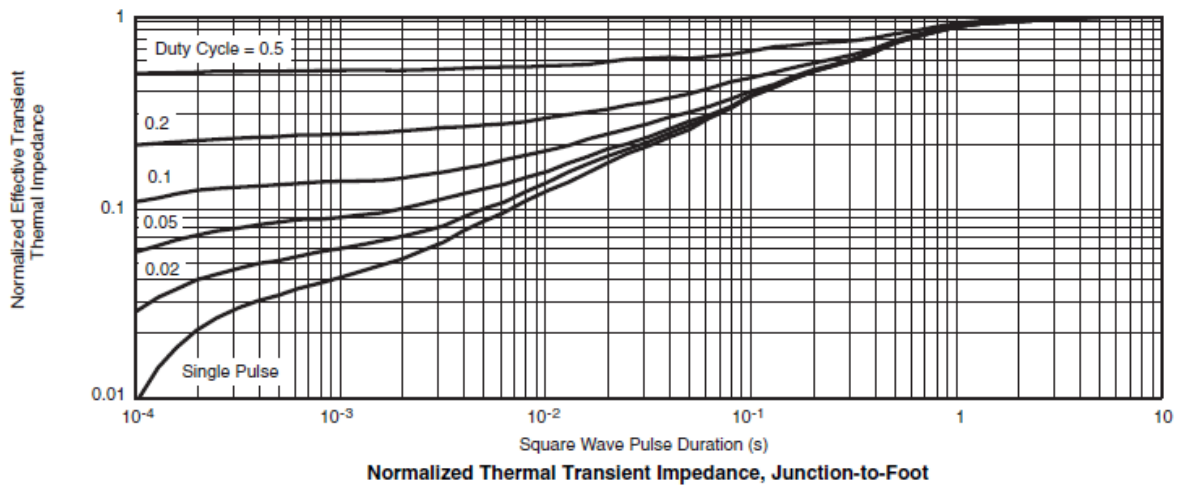
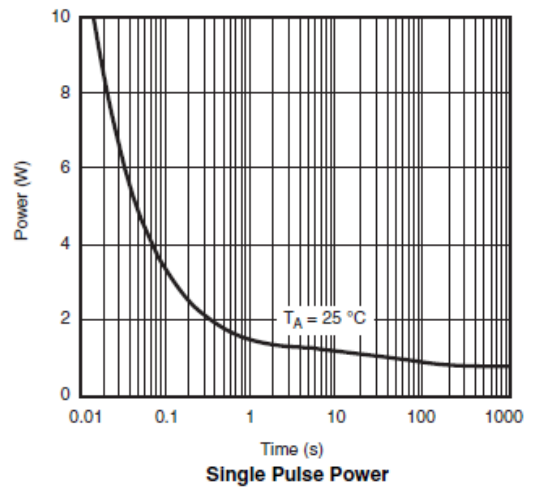
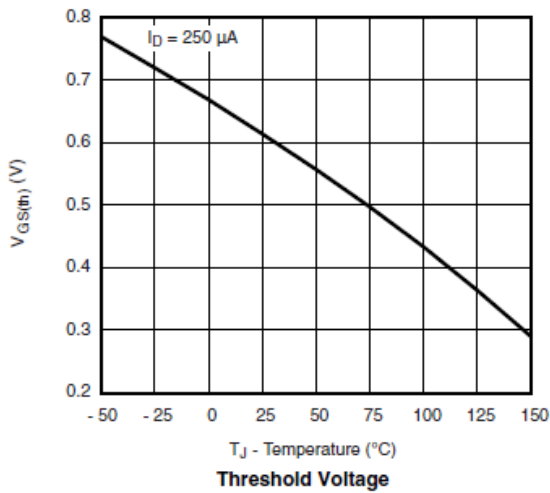
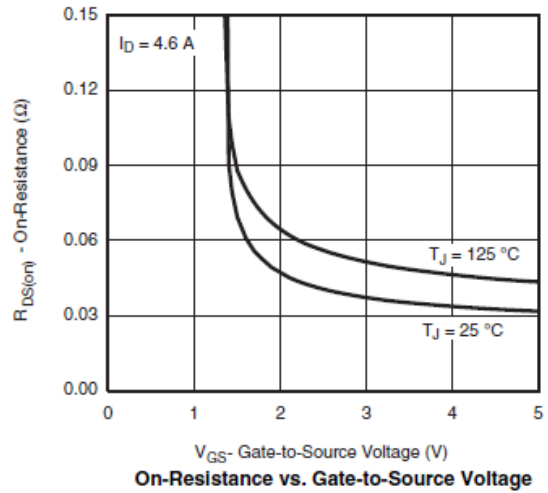
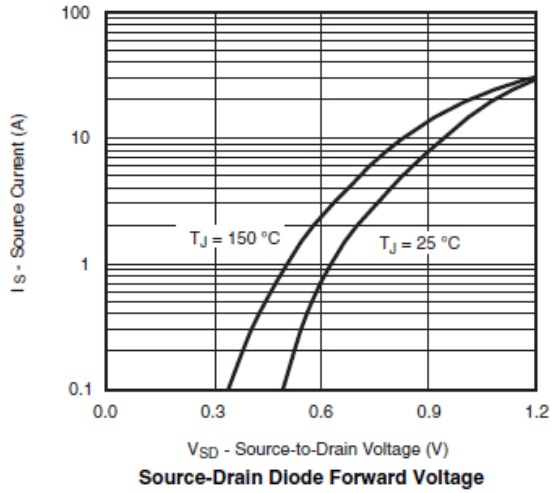
Gate Charge



On-Resistance vs. Junction Temperature



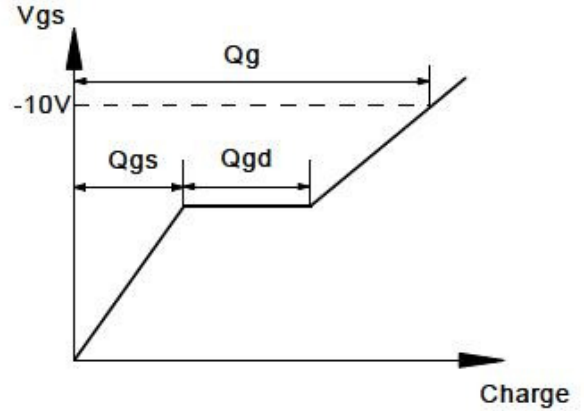
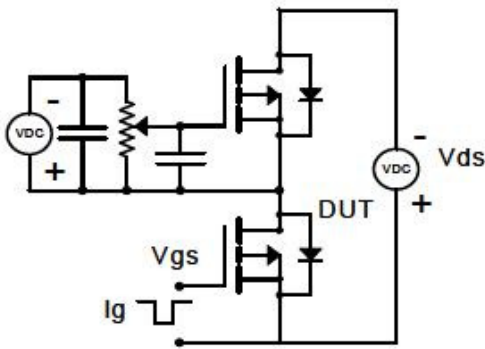
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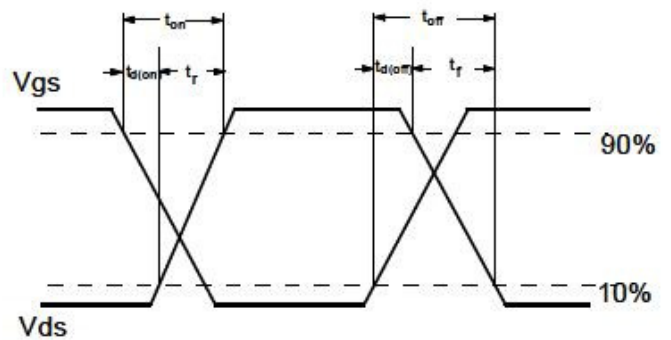
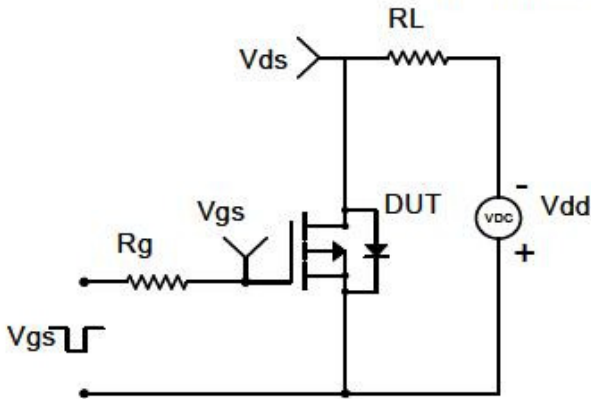


## Typical Characteristics

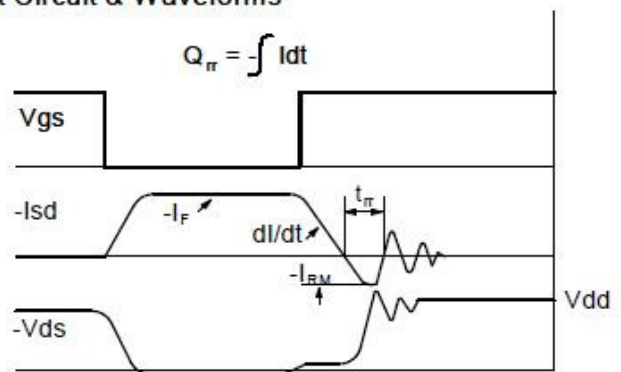
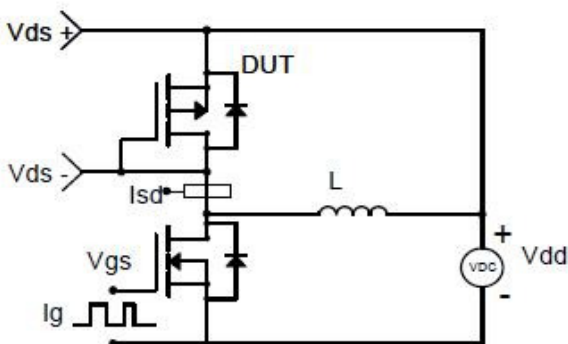
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

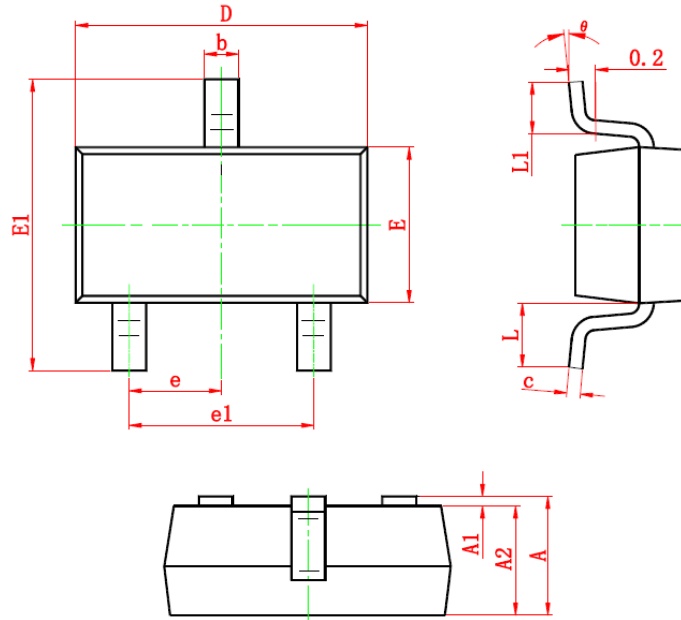


### Diode Recovery Test Circuit & Waveforms





**Package Information ( SOT-23 )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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